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1. (Amended) A fabrication method for a multi-layered thin film protective layer, which is applicable to a substrate comprising a first device area and a second device area, the method comprising the steps of:

forming a first protective layer on the first device area, wherein the first protective layer prevents the first device area from moisture and scratch;

forming a plurality of material structures on the first protective layer, the material structures and the underlying first protective layer serving as first pad spacers;

forming a plurality of oxide material/silicon nitride/oxide material structures on the second device area serving as second pad spacers in the second device area, wherein the second pad spacers are higher than the first protective layer; and

forming a second protective layer for at least covering the second device area, wherein a transparency of the second protective layer is higher than a transparency of the first protective layer.

2. (Amended) The fabrication method for a multi-layered thin film protective layer according to claim 1, further including:

forming sequentially a first oxide layer, a silicon nitride layer and a second oxide layer on the substrate;

patterning the second oxide material to form material structures and upper oxide material of the material/silicon nitride/oxide material structures;

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patterning the silicon nitride layer and the first oxide layer to form a silicon nitride/oxide material structure as the first protective layer in the first device area and to form a bottom oxide material and a silicon nitride of the material/silicon nitride/oxide material structures; and

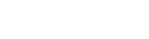
forming a third oxide layer on the substrate as a second protective layer.

- 3. (Amended) The fabrication method for a multi-layered thin film protective layer according to claim 2, wherein the transparency of the second protective layer is approximately 85%.
- 4. (Amended) The fabrication method for a multi-layered thin film protective layer according to claim \$\frac{1}{2}\$, wherein the third oxide layer is approximately 500\hat{A} thick.
- 5. (Amended) The fabrication method for a multi-layered thin film protective layer according to claim 2, wherein the third oxide layer includes tetra-ethyl-ortho-silicate.

Please add the following new claims:

(Newly Added) A fabrication method for a multi-layered thin film protective layer, which is applicable to a substrate comprising a first device area and a second device area, the method comprising the steps of:

forming a first protective layer on the first device area, wherein the first protective layer prevents moisture penetration and scratching;









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forming a plurality of material structures on the first protective layer, the material structures and the underlying first protective layer serving as first pad spacers;

forming a plurality of multi-layered material structures on the second device area serving as second pad spacers in the second device area, wherein the second pad spacers are higher than the first protective layer; and

forming a second protective layer at least covering the second device area, wherein a transparency of the second protective layer is higher than a transparency of the first protective layer.

(Newly Added) The fabrication method for a multi-layered thin film protective layer according to claim \$6, further including:

forming sequentially a first layer, a second layer and a third layer on the substrate;

patterning the third layer to form the material structures and a upper layer of the multilayered material structures;

patterning the second layer and the first layer to form the first protective layer in the first device area and to form the bottom layers of the material/silicon nitride/oxide material structures; and

forming a second protective layer covering the first device area and the second device area, wherein the second protective layer second protective layer

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20 8. (Newly Added) The fabrication method for a multi-layered thin film protective layer according to claim \$6, wherein the second protective layer is thinner than any layers of the multilayered material structures.

(Newly Added) The fabrication method for a multi-layered thin film protective layer according to claim , wherein the first protective layer at least comprises an oxide layer and a silicon oxide layer on the oxide layer.

(Newly Added) The fabrication method for a multi-layered thin film protective layer according to claim, wherein the second protective layer comprises an oxide layer.